

In the claims:

1. Canceled.

2. (Currently amended) A method according to claim 10 +, in which said heating power is supplied by an upper set of lamps disposed above said workpiece and a lower set of lamps disposed below said substrate.

3. (Currently amended) A method of forming a layer of silicon on a surface of a workpiece comprising the steps of:

heating said workpiece on a substrate in a vacuum chamber;

depositing a layer of silicon on a surface of said workpiece;

in which said step of heating comprises supplying more than half of a total heating power to a lower surface of said workpiece in which said heating power is supplied by an upper set of lamps disposed above said workpiece and a lower set of lamps disposed below said substrate, whereby said workpiece is maintained at a deposition temperature greater than a crystallization temperature of silicon during the depositing of the layer of silicon ~~A method according to claim 2~~, in which approximately eighty percent of said heating power is supplied to said lower set of lamps.

4. (Currently amended) A method according to claim 10 +, in which said substrate is maintained at a temperature of greater than 690°C.

5. (Original) A method according to claim 2, in which said substrate is maintained at a temperature of greater than 690°C.

6. (Original) A method according to claim 3, in which said substrate is maintained at a temperature of greater than 690°C.

7. (Currently amended) A method according to claim 3 4, in which said substrate is maintained at a temperature of less than 710°C.

8. (Currently amended) A method according to claim 10 5, in which said substrate is maintained at a temperature of less than 710°C.

9. (Original) A method according to claim 6, in which said substrate is maintained at a temperature of less than 710°C.

10. (Currently amended) A method of forming a layer of silicon on a surface of a workpiece comprising the steps of:

heating said workpiece on a substrate in a vacuum chamber;

depositing a layer of silicon on a surface of said workpiece;

A method according to claim 1, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece, whereby said workpiece is maintained at a deposition temperature greater than a crystallization temperature of silicon during the depositing of the layer of silicon.

11 to 20 Canceled.